

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1-11 (canceled)

12. (original) A method of fabricating a capacitor on a substrate comprising the steps of:

- performing capacitor foundation formation on the substrate;
- depositing polish stop layer material on the capacitor foundation and the substrate;
- etching a first capacitor electrode region on the capacitor foundation formation and a transistor gate region on the substrate;
- depositing a first conductive material in the etched first capacitor electrode region and the transistor gate region;
- performing chemical mechanical polishing on the deposited first conductive material to yield a gate electrode and a first capacitor electrode;
- depositing a dielectric material over the gate electrode and the first capacitor electrode;
- etching a second capacitor electrode region in the dielectric material over the first capacitor electrode and into the first capacitor electrode material;
- forming a capacitor dielectric layer over the first capacitor electrode;

depositing a second conductive material in the etched second capacitor electrode region; and

performing chemical mechanical polishing on the deposited second conductive material to yield a second capacitor electrode.

13. (original) The method of claim 12, wherein the step of depositing polish stop layer material on the capacitor foundation substrate includes depositing polish stop layer material comprising an oxide.

14. (original) The method of claim 12, wherein the step of depositing polish stop layer material on the capacitor foundation substrate includes depositing polish stop layer material comprising a nitride.

15. (original) The method of claim 12, wherein the steps of performing chemical mechanical polishing on the deposited first conductive material to yield a first capacitor electrode yields a first electrode in the form of a plate, and performing chemical mechanical polishing on the deposited second conductive material to yield a second capacitor electrode yields a second electrode in the form of a plate.

16. (original) The method of claim 12, wherein the steps of performing chemical mechanical polishing on the deposited first conductive material to yield a first capacitor electrode yields a first substantially cylindrical electrode and performing chemical mechanical polishing on the deposited second conductive material to yield a second capacitor electrode yields a second substantially cylindrical electrode.

II. Conclusion

Claims 12-16 are pending in this application. By this amendment, claims 1-11 have been canceled. Applicants respectfully request entry of the amendment and favorable consideration of the application.

A prompt and favorable action on the merits is requested.

Respectfully Submitted,



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